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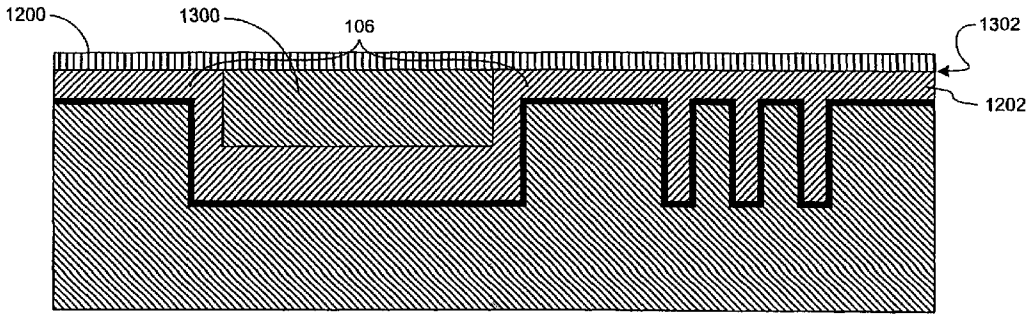
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(54) Title: METHOD AND APPARATUS TO FORM A PLANARIZED CU INTERCONNECT LAYER USING ELECTROLESS MEMBRANE DEPOSITION



(57) Abstract: A planarized conductive material is formed over a substrate including narrow (108) and wide (106) features. The conductive material is formed through a succession of deposition processes. A first deposition process forms a first layer (600) of the conductive material that fills the narrow features and at least partially fills the wide features. A second deposition process forms a second layer (700) of the conductive material within recesses in the first layer. Polishing with a flexible material (1200) can reduce a thickness of the first layer above the substrate while delivering a solution to the recesses to form the second layer therein. The flexible material can be a porous membrane attached to a pressurizable reservoir filled with the solution. The flexible material can also be a poromeric material wetted with the solution.

WO 2004/088746 A3